EMC TEST REPORT

Product	:	Micro sd card
Trade mark	:	LansTen
Model/Type reference	:	256GB, 128MB, 256MB, 512MB, 1GB, 2GB, 4GB, 8GB, 16GB, 32GB, 50GB, 64GB, 100GB, 128GB, 200GB
Serial Number	:	N/A
Ratings	:	Power by main board
Report Number	:	EED32S810649
Date of Issue	:	May 21, 2026
Regulations	:	See below

Test Standards	Results
EN 55032:2015+A11:2020	PASS
EN 55035:2017+A11:2020	PASS

Prepared for:

Shenzhen Xinaoxin Technology Co., Ltd
1819, Building B, Tianxia International Center, No.8 Taoyuan Road, Dawangshan Community Nantou Street, Nanshan District, Shenzhen

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Approved by: David Wang Date of Issue: May 21, 2026

Aaron Ma Check No.: 7025130526

Modification Record

Version No.	Report No.	Modification Description
00	EED32Q815744	Last report
01	EED32S810649	Add product appearance photo(Only the appearance and colour are different)
Note: All test data come from the report of No. EED32Q815744.		

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(Note: N/A means not applicable)

1. GENERAL INFORMATION

Applicant:	Shenzhen Xinaoxin Technology Co., Ltd 1819, Building B, Tianxia International Center, No.8 Taoyuan Road, Dawangshan Community Nantou Street, Nanshan District, Shenzhen
Manufacturer:	Shenzhen Xinaoxin Technology Co., Ltd 1819, Building B, Tianxia International Center, No.8 Taoyuan Road, Dawangshan Community Nantou Street, Nanshan District, Shenzhen
EMC Directive:	2014/30/EU
Product:	Micro sd card
Trade mark:	LansTen
Model/Type reference:	256GB, 128MB, 256MB, 512MB, 1GB, 2GB, 4GB, 8GB, 16GB, 32GB, 50GB, 64GB, 100GB, 128GB, 200GB
Serial Number:	N/A
Report Number:	EED32S810649
State of Sample(s):	Normal
Sample Received Date:	Oct. 11, 2024
Sample tested Date:	Oct. 11, 2024 to Oct. 12, 2024

Company Name and Address shown on report, the sample(s) and sample Information was/ were provided by the applicant who should be responsible for the authenticity which CTI hasn't verified.

2. TEST SUMMARY

The Product has been tested according to the following specifications:

EMISSION		
Standard	**Test Item**	**Test**
EN 55032	Conducted disturbance	N/A[1]
EN 55032	Radiated disturbance	Yes

IMMUNITY (EN 55035)		
Standard	**Test Item**	**Test**
IEC 61000-4-2	Electrostatic discharge (ESD)	Yes
IEC 61000-4-3	Continuous RF electromagnetic radiated field disturbances	Yes
IEC 61000-4-4	Electrical fast transients (EFT)	N/A[1]
IEC 61000-4-5	Surges	N/A[1]
IEC 61000-4-6	Radio-frequency continuous conducted Immunity	N/A[1]
IEC 61000-4-8	Power-frequency magnetic fields Immunity	N/A[2]
IEC 61000-4-11	Voltage dips and interruptions	N/A[1]

Remark:
1. The Product is powered By main board, the test is not applicable.
2. The Product doesn't contain any device susceptible to magnetic fields.

3. TEST UNCERTAINTY

Where relevant, the following test uncertainty levels have been estimated for tests performed on the Product as specified in CISPR 16-4-2. This uncertainty represents an expanded uncertainty expressed at approximately the 95% confidence level using a coverage factor of k=2.

Test item	Value (dB)
Radiated emissions (30MHz to 1GHz)	4.9
Radiated emissions (Above 1GHz)	4.7

4. PRODUCT INFORMATION AND TEST SETUP

4.1 PRODUCT INFORMATION

Ratings: Power by main board

Model difference: They have same electrical, PCB and layout, only the model name is different for marketing requirements. The test model is 256GB, and the test results are applicable to the others.

The highest frequency of the internal sources of the EUT is Above 500MHz, less than 1GHz:

☐ less than or equal 108 MHz, the measurement shall only be made up to 1 GHz.
☐ between 108 MHz and 500 MHz, the measurement shall only be made up to 2 GHz.
☒ between 500 MHz and 1 GHz, the measurement shall only be made up to 5 GHz.
☐ above 1 GHz, the measurement shall be made up to 5 times the highest frequency up to a maximum of 6GHz.

4.2 TEST SETUP CONFIGURATION

See test photographs attached in Appendix 1 for the actual connections between product and support equipment.

4.3 TEST MODE DESCRIPTION

Test Mode	Test Status
①	Data transmissions mode:EUT connected to laptop and running test program for data transmission.

4.4 SUPPORT EQUIPMENT

No.	Device Type	Brand	Series No.	Model	Data Cable	Power Cord
1.	Netbook	HP	5CG5192QVB	HP 340G2	----	----

Notes:

1. All the equipment/cables were placed in the worst-case configuration to maximize the emission during the test.
2. Grounding was established in accordance with the manufacturer's requirements and conditions for the intended use.

5. FACILITIES AND ACCREDITATIONS

5.1 TEST FACILITY

All test facilities used to collect the test data are located at Hongwei Industrial Zone, Bao'an 70 District, Shenzhen, Guangdong, China. The site and apparatus are constructed in conformance with the requirements of ANSI C63.4, CISPR 16-1-1 and other equivalent standards.

5.2 TEST EQUIPMENT LIST

Instrumentation: The following list contains equipment used at CTI for testing.
The calibrations of the measuring instruments, including any accessories that may affect such calibration, are checked frequently to assure their accuracy. Adjustments are made and correction factors applied in accordance with instructions contained in the manual for the measuring instrument.

Equipment used during the tests:

3M Semi-anechoic Chamber (2)_Hongwei-Radiated emissions				
Equipment	**Manufacturer**	**Model**	**Series No.**	**Due Date**
3M Chamber & Accessory Equipment	TDK	SAC-3	--	01/12/2027
Receiver	R&S	ESR7	101697	09/18/2025
TRILOG Broadband Antenna	Schwarzbeck	VULB9163	9163-401	09/13/2025
Microwave Preamplifier	Tonscend	EMC051845SE	980380	12/13/2024
Horn Antenna	Schwarzbeck	BBHA 9120D	9120D-1869	04/15/2025
Software-EZ	Farad Technology	--	EMEC-3A1-Pre	--

Shielding Room No. 1_Hongwei-Electrostatic discharge (ESD)				
Equipment	**Manufacturer**	**Model**	**Series No.**	**Due Date**
ESD Simulator	TESEQ	NSG437	1182	06/02/2025

3M Semi-anechoic Chamber (1)_Hongwei-Continuous RF electromagnetic radiated field disturbances				
Equipment	**Manufacturer**	**Model**	**Series No.**	**Due Date**
3M Chamber & Accessory Equipment	ETS-LINDGREN	FACT-3	3510	05/19/2025
Signal Generator	R&S	SMB 100B	103084	05/12/2025
Horn Antenna	Schwarzbeck	STLP 9149	0776	06/05/2026
Stacked double Log.-Per. Antenna	Schwarzbeck	STLP9128	9128ES-110	03/21/2026
Directional coupler	BONN	BDC 1060-40/500	2128343-04	11/26/2024
RF switch	R&S	OSP220	102205	--
Power Amplifier	BONN	BLMA 1060-100	2113427	07/21/2025
Power Amplifier	R&S	BBA 150-BC500	104743	05/30/2025
Power Probe	R&S	NRP6A	103343	06/24/2025
Power Probe	R&S	NRP6A	103342	06/24/2025
Software-EMC-32	R&S	--	V10.60.20-Y267_FU	--

5.3 LABORATORY ACCREDITATIONS AND LISTINGS

The measuring equipment utilized to perform the tests documented in this report has been calibrated once a year or in accordance with the manufacturer's recommendations and is traceable under the ISO/IEC 17025 to international or national standards. Equipment has been calibrated by accredited calibration laboratories.

6. RADIATED EMISSIONS

6.1 LIMITS

30MHz ~ 1GHz(3m):

Requirements for radiated emissions for Class B equipment

Frequency (MHz)	Quasi-peak limits at 3m dB(μV/m)
30-230	40
230-1000	47

Above 1G(3m&10m):

Requirements for radiated emissions for Class B equipment

Frequency (GHz)	limit above 1GHz at 3m dB(μV/m)	
	Average	peak
1-3	50	70
3-6	54	74

NOTE: The lower limit shall apply at the transition frequency.

6.2 BLOCK DIAGRAM OF TEST SETUP

30MHz ~ 1GHz(3m):

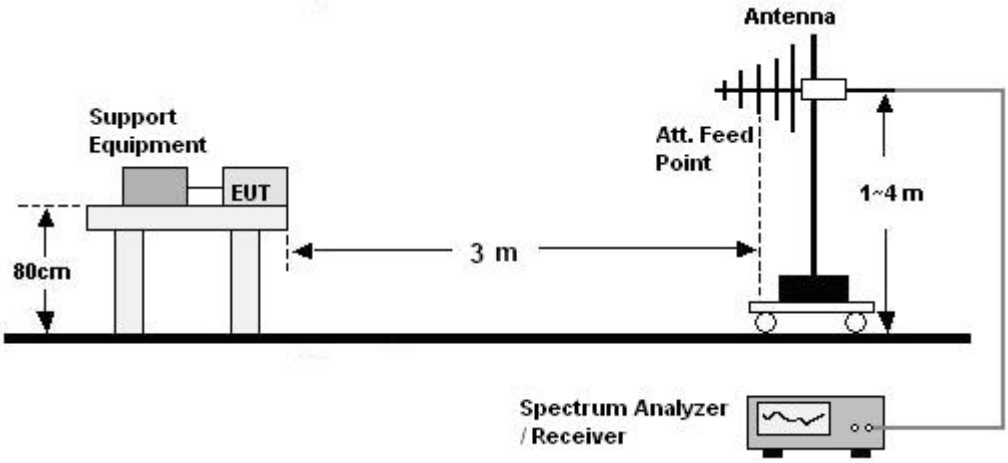


Table Top

Above 1GHz:

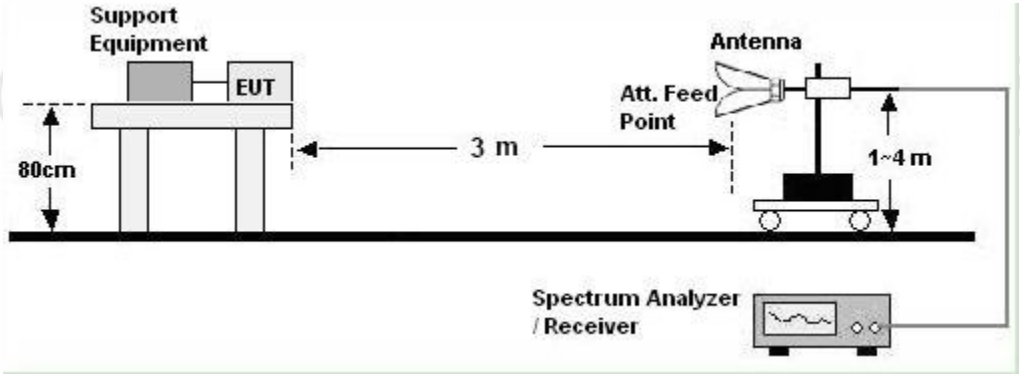


Table Top

6.3 TEST PROCEDURE

30MHz ~ 1GHz(Table Top**):**
a. The Product was placed on the non-conductive turntable 0.8 m above the ground at a chamber.

b. Set the spectrum analyzer/receiver in Peak detector, Max Hold mode, and 120 kHz RBW. Record the maximum field strength of all the pre-scan process in the full band when the antenna is varied between 1~4 m in both horizontal and vertical, and the turntable is rotated from 0 to 360 degrees.

c. For each frequency whose maximum record was higher or close to limit, measure its QP value: vary the antenna's height and rotate the turntable from 0 to 360 degrees to find the height and degree where Product radiated the maximum emission, then set the test frequency analyzer/receiver to QP Detector and specified bandwidth with Maximum Hold Mode, and record the maximum value.

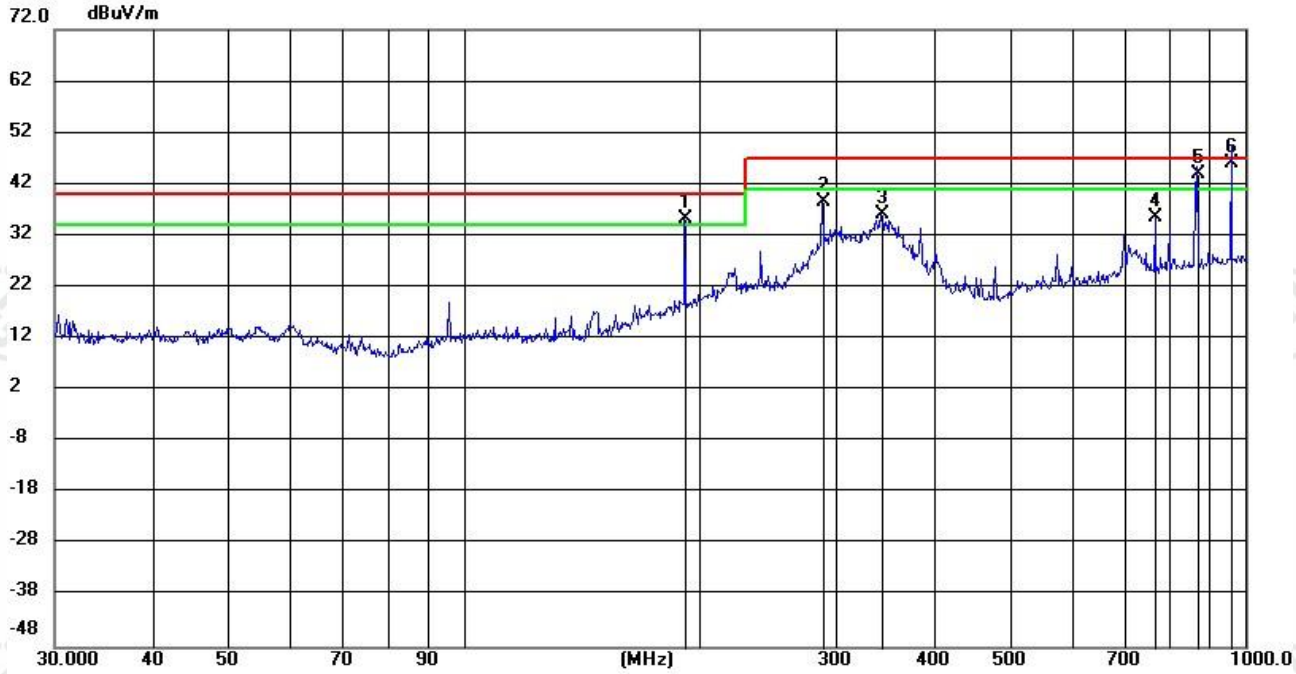
Above 1GHz(Table Top**):**
a. The Product was placed on the non-conductive turntable 0.8 m above the ground at a chamber.

b. Set the spectrum analyzer/receiver in Peak detector, Max Hold mode, and 1MHz RBW. Record the maximum field strength of all the pre-scan process in the full band when the antenna is varied in both horizontal and vertical, and the turntable is rotated from 0 to 360 degrees.

c. For each frequency whose maximum record was higher or close to limit, measure its AV value: rotate the turntable from 0 to 360 degrees to find the degree where Product radiated the maximum emission, then set the test frequency analyzer/receiver to AV value and specified bandwidth with Maximum Hold Mode, and record the maximum value.

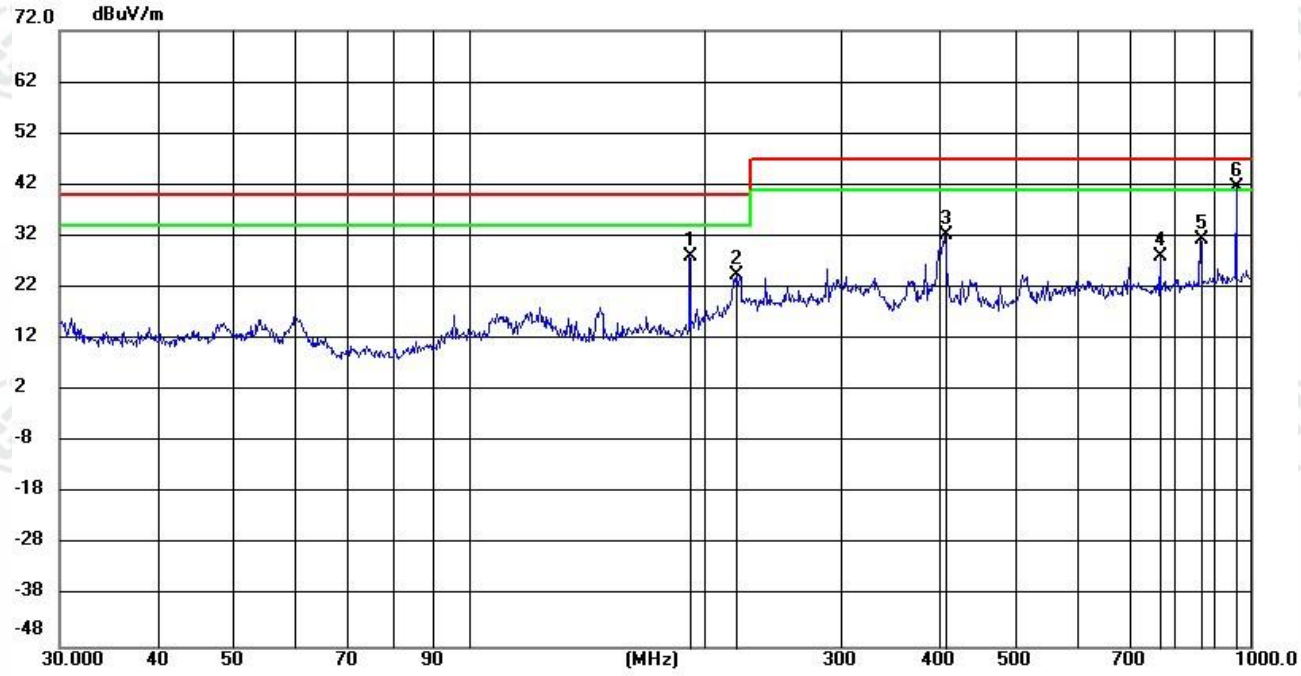
6.4 GRAPHS AND DATA

Product	:	Micro sd card			
Model/Type reference	:	256GB			
Power	:	DC 5V	**Temperature**	:	23℃
Mode	:	①	**Humidity**	:	54%R.H.
Polarization	:	Horizontal	**Press**	:	101KPa



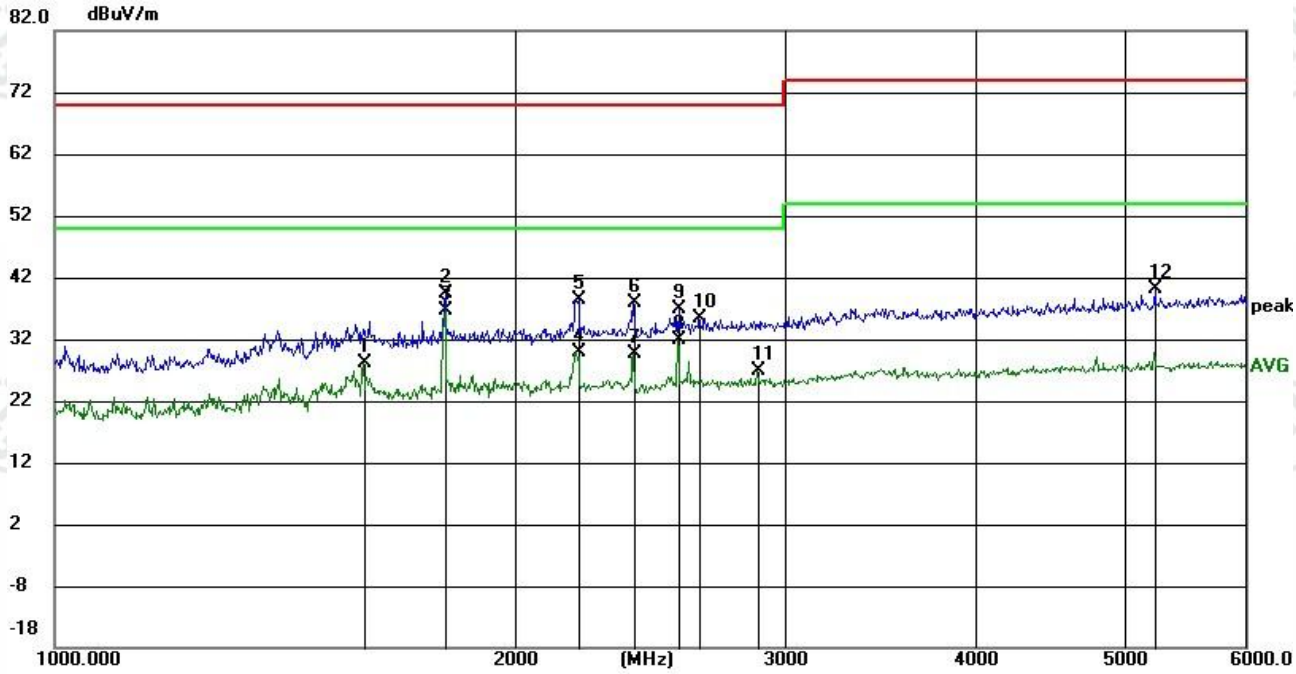
No.	Mk.	Freq.	Reading Level	Correct Factor	Measurement	Limit	Margin		Antenna Height	Table Degree
		MHz	dBuV	dB/m	dBuV/m	dBuV/m	dB	Detector	cm	degree
1	!	192.0141	23.24	12.03	35.27	40.00	-4.73	QP	200	310
2		288.0409	22.93	15.70	38.63	47.00	-8.37	QP	100	7
3		342.6989	19.24	16.96	36.20	47.00	-10.80	QP	100	7
4		768.0745	11.45	24.02	35.47	47.00	-11.53	QP	100	136
5	!	868.5209	18.40	25.47	43.87	47.00	-3.13	QP	200	144
6	*	960.1400	19.73	26.27	46.00	47.00	-1.00	QP	100	335

Product	:	Micro sd card			
Model/Type reference	:	256GB			
Power	:	DC 5V	**Temperature**	:	23℃
Mode	:	①	**Humidity**	:	54%R.H.
Polarization	:	Vertical	**Press**	:	101KPa



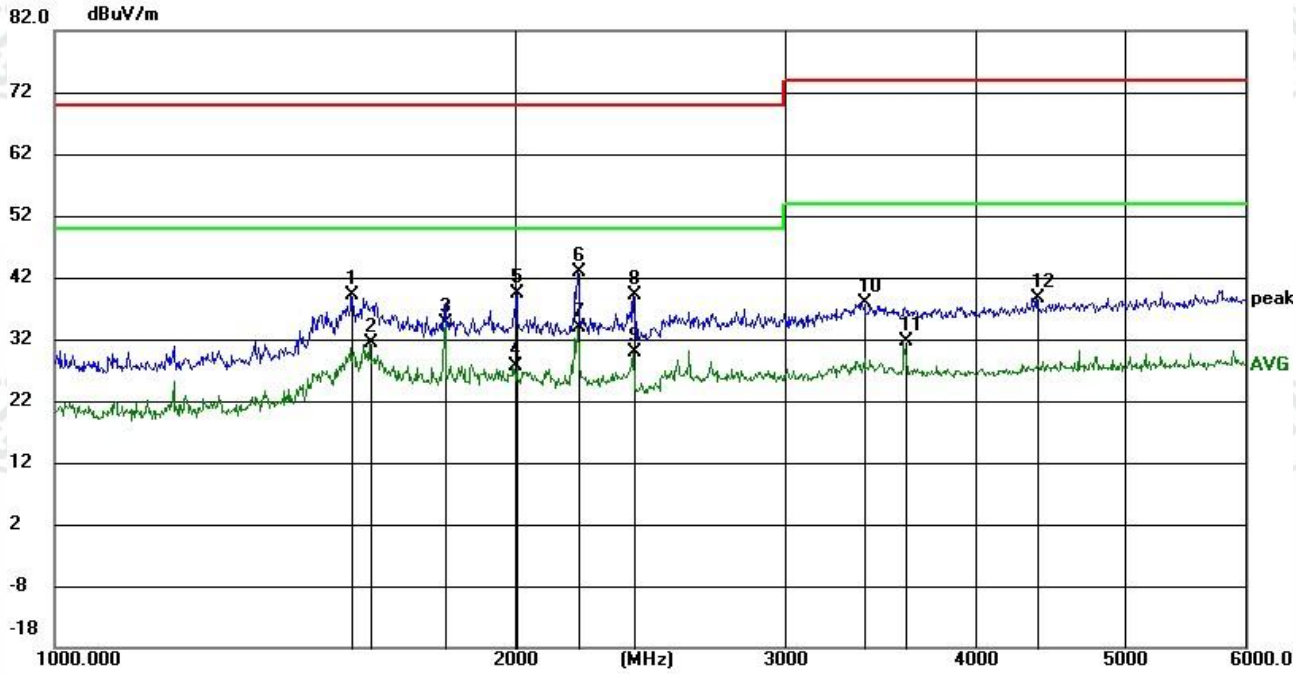
No.	Mk.	Freq.	Reading Level	Correct Factor	Measurement	Limit	Margin		Antenna Height	Table Degree
		MHz	dBuV	dB/m	dBuV/m	dBuV/m	dB	Detector	cm	degree
1		192.0142	17.36	10.58	27.94	40.00	-12.06	QP	200	201
2		220.3852	12.97	11.57	24.54	40.00	-15.46	QP	200	170
3		407.3002	16.27	16.01	32.28	47.00	-14.72	QP	100	164
4		768.0745	6.99	20.92	27.91	47.00	-19.09	QP	200	170
5		864.1161	9.16	22.13	31.29	47.00	-15.71	QP	100	352
6	*	960.1401	18.67	22.90	41.57	47.00	-5.43	QP	100	352

Product	:	Micro sd card			
Model/Type reference	:	256GB			
Power	:	DC 5V	**Temperature**	:	23℃
Mode	:	①	**Humidity**	:	54%R.H.
Polarization	:	Horizontal	**Press**	:	101KPa



No.	Mk.	Freq.	Reading Level	Correct Factor	Measurement	Limit	Margin		Antenna Height	Table Degree
		MHz	dBuV	dB/m	dBuV/m	dBuV/m	dB	Detector	cm	degree
1		1592.952	42.56	-14.32	28.24	50.00	-21.76	AVG	100	180
2		1800.000	52.24	-12.76	39.48	70.00	-30.52	peak	100	128
3	*	1800.000	49.32	-12.76	36.56	50.00	-13.44	AVG	100	128
4		2197.650	39.89	-10.05	29.84	50.00	-20.16	AVG	100	180
5		2200.014	48.55	-10.05	38.50	70.00	-31.50	peak	100	76
6		2390.094	46.72	-8.89	37.83	70.00	-32.17	peak	100	76
7		2390.094	38.48	-8.89	29.59	50.00	-20.41	AVG	100	76
8		2560.330	39.90	-8.01	31.89	50.00	-18.11	AVG	100	7
9		2560.559	44.92	-8.01	36.91	70.00	-33.09	peak	100	111
10		2640.463	43.06	-7.70	35.36	70.00	-34.64	peak	100	163
11		2880.186	33.80	-6.81	26.99	50.00	-23.01	AVG	100	7
12		5244.597	39.82	0.30	40.12	74.00	-33.88	peak	100	128

Product	:	Micro sd card			
Model/Type reference	:	256GB			
Power	:	DC 5V	**Temperature**	:	23℃
Mode	:	①	**Humidity**	:	54%R.H.
Polarization	:	Vertical	**Press**	:	101KPa



No.	Mk.	Freq.	Reading Level	Correct Factor	Measurement	Limit	Margin		Antenna Height	Table Degree
		MHz	dBuV	dB/m	dBuV/m	dBuV/m	dB	Detector	cm	degree
1		1563.123	53.74	-14.55	39.19	70.00	-30.81	peak	100	149
2		1609.592	45.49	-14.19	31.30	50.00	-18.70	AVG	100	149
3	*	1800.000	47.37	-12.76	34.61	50.00	-15.39	AVG	100	115
4		1997.662	38.96	-11.27	27.69	50.00	-22.31	AVG	100	149
5		2004.115	50.61	-11.23	39.38	70.00	-30.62	peak	100	166
6		2197.650	53.05	-10.05	43.00	70.00	-27.00	peak	100	47
7		2197.650	44.01	-10.05	33.96	50.00	-16.04	AVG	100	47
8		2389.880	47.93	-8.89	39.04	70.00	-30.96	peak	100	250
9		2389.880	38.69	-8.89	29.80	50.00	-20.20	AVG	100	250
10		3375.707	42.48	-4.55	37.93	74.00	-36.07	peak	100	183
11		3599.982	35.53	-3.78	31.75	54.00	-22.25	AVG	100	115
12		4390.556	40.53	-1.97	38.56	74.00	-35.44	peak	100	149

Note:
1. Margin=Measurement-Limit.
2. Measurement=Reading Level+Correct Factor.

7. IMMUNITY TEST

General Performance Criteria	
Product Standard	**EN 55035:2017+A11:2020 clause 8**
CRITERION A	The equipment shall continue to operate as intended without operator intervention. No degradation of performance, loss of function or change of operating state is allowed below a performance level specified by the manufacturer when the equipment is used as intended. The performance level may be replaced by a permissible loss of performance. If the minimum performance level or the permissible performance loss is not specified by the manufacturer, then either of these may be derived from the product description and documentation, and by what the user may reasonably expect from the equipment if used as intended.
CRITERION B	During the application of the disturbance, degradation of performance is allowed. However, no unintended change of actual operating state or stored data is allowed to persist after the test. After the test, the equipment shall continue to operate as intended without operator intervention; no degradation of performance or loss of function is allowed, below a performance level specified by the manufacturer, when the equipment is used as intended. The performance level may be replaced by a permissible loss of performance. If the minimum performance level (or the permissible performance loss), or recovery time, is not specified by the manufacturer, then either of these may be derived from the product description and documentation, and by what the user may reasonably expect from the equipment if used as intended.
CRITERION C	Loss of function is allowed, provided the function is self-recoverable, or can be restored by the operation of the controls by the user in accordance with the manufacturer's instructions. A reboot or re-start operation is allowed. Information stored in non-volatile memory, or protected by a battery backup, shall not be lost.

7.1 ELECTROSTATIC DISCHARGES (ESD)

7.1.1 TEST SPECIFICATION

Basic Standard	:	EN 55035 & IEC 61000-4-2
Test Port	:	Enclosure port
Discharge Impedance	:	330 ohm / 150 pF
Discharge Mode	:	Single Discharge
Discharge Period	:	one second between each discharge

7.1.2 BLOCK DIAGRAM OF TEST SETUP

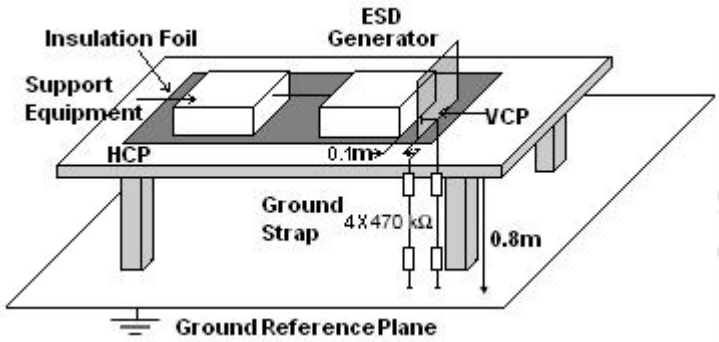


Table Top

7.1.3 TEST PROCEDURE

a. Electrostatic discharges were applied only to those points and surfaces of the product that are accessible to users during normal operation.

b. The test was performed with at least ten single discharges on the pre-selected points in the most sensitive polarity.

c. The time interval between two successive single discharges was at least 1 second.

d. The ESD generator was held perpendicularly to the surface to which the discharge was applied, and the return cable was at least 0.2 meters from the Product.

e. Contact discharges were applied to the non-insulating coating, with the pointed tip of the generator penetrating the coating and contacting the conducting substrate.

f. Air discharges were applied with the round discharge tip of the discharge electrode approaching the Product as fast as possible (without causing mechanical damage) to touch the Product. After each discharge, the ESD generator was removed from the product and re-triggered for a new single discharge. The test was repeated until all discharges were complete.

g. At least ten single discharges (in the most sensitive polarity) were applied to the Horizontal Coupling Plane at points on each side of the Product. The ESD generator was positioned vertically at a distance of 0.1 meters from the Product with the discharge electrode touching the HCP.

h. At least ten single discharges (in the most sensitive polarity) were applied to the center of one vertical edge of the Vertical Coupling Plane in sufficiently different positions that the four faces of the product were completely illuminated. The VCP (dimensions 0.5m x 0.5m) was placed vertically to and 0.1 meters from the product.

7.1.4 RESULTS & PERFORMANCE

Product	:	Micro sd card			
Model/Type reference	:	256GB			
Power	:	DC 5V	**Temperature**	:	24℃
Mode	:	①	**Humidity**	:	55%R.H.
Press	:	101kPa			

Discharge Method	Discharge Position	Voltage(±kV)	Min. No. of Discharge per polarity(Each Point)	Performance Criterion	Test Result
Contact Discharge	Conductive Surfaces	4	10	B	A
Contact Discharge	Indirect Discharge HCP	4	10	B	A
Contact Discharge	Indirect Discharge VCP	4	10	B	A
Air Discharge	Apertures and Insulating Surfaces	8	10	B	A

Note: No observable degradation in performance.

7.2 CONTINUOUS RF ELECTROMAGNETIC RADIATED FIELD DISTURBANCES

7.2.1 TEST SPECIFICATION

Basic Standard	:	EN 55035 & IEC 61000-4-3
Test Port	:	Enclosure port
Sweep Step	:	1%
Dwell Time	:	1s
Modulation	:	1 kHz 80% AM

7.2.2 BLOCK DIAGRAM OF TEST SETUP

80-1000MHz:

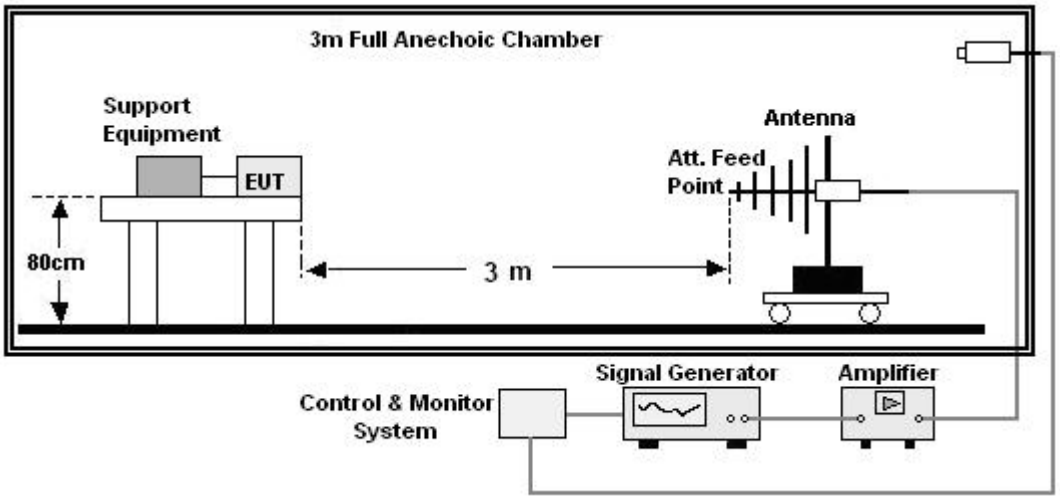


Table Top

Above 1000MHz:

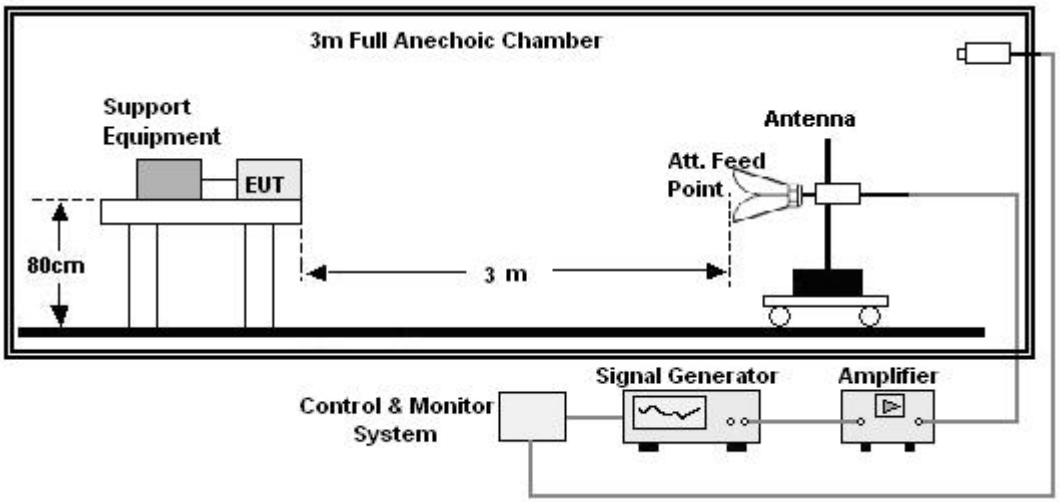


Table Top

7.2.3 TEST PROCEDURE

a. The testing was performed in a fully anechoic chamber. The transmit antenna was located at a distance of 3 meters from the Product.

b. The frequency range is swept from 80MHz to 1000MHz, 1800MHz, 2600MHz, 3500MHz, 5000MHz with the signal 80% amplitude modulated with a 1 kHz sine wave. The rate of

sweep did not exceed 1.5x 10^{-3} decade/s. Where the frequency range is swept incrementally, the step size was 1%.

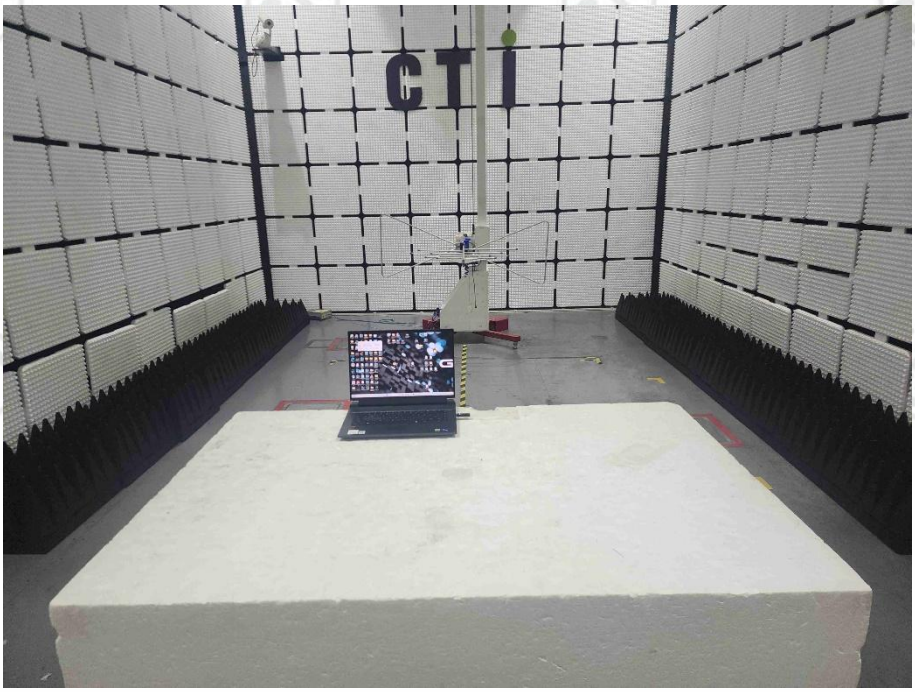
c. The test was performed with the Product exposed to both vertically and horizontally polarized fields on each of the four sides.

7.2.4 RESULTS & PERFORMANCE

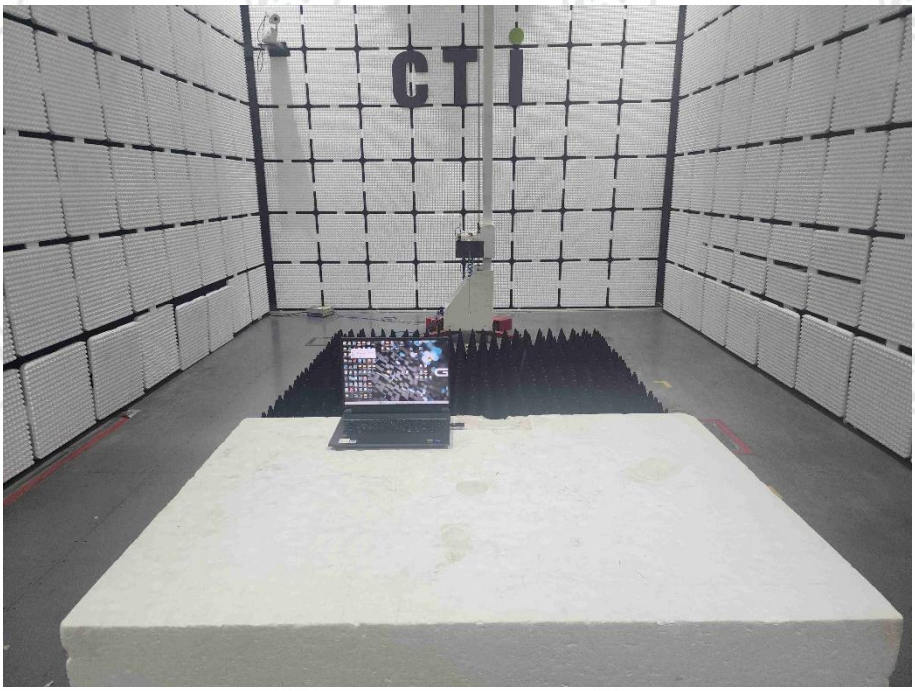
Product	:	Micro sd card			
Model/Type reference	:	256GB			
Power	:	DC 5V	**Temperature**	:	22℃
Mode	:	①	**Humidity**	:	56%R.H.
Press	:	101kPa			

Frequency(MHz)	Position	Field Strength(V/m)	Performance Criterion	Test Result
80 - 1000	Front,Right,Back,Left	3	A	A
1800	Front,Right,Back,Left	3	A	A
2600	Front,Right,Back,Left	3	A	A
3500	Front,Right,Back,Left	3	A	A
5000	Front,Right,Back,Left	3	A	A

APPENDIX 1 PHOTOGRAPHS OF TEST SETUP



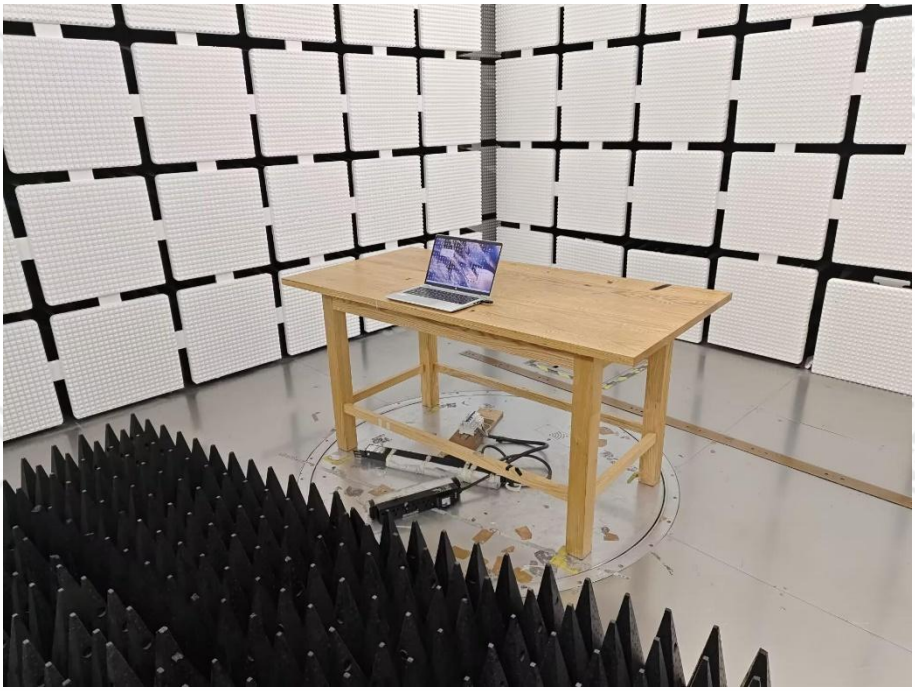
Radiated emissions Test Setup-1



Radiated emissions Test Setup-2



Electrostatic discharge Test Setup-1

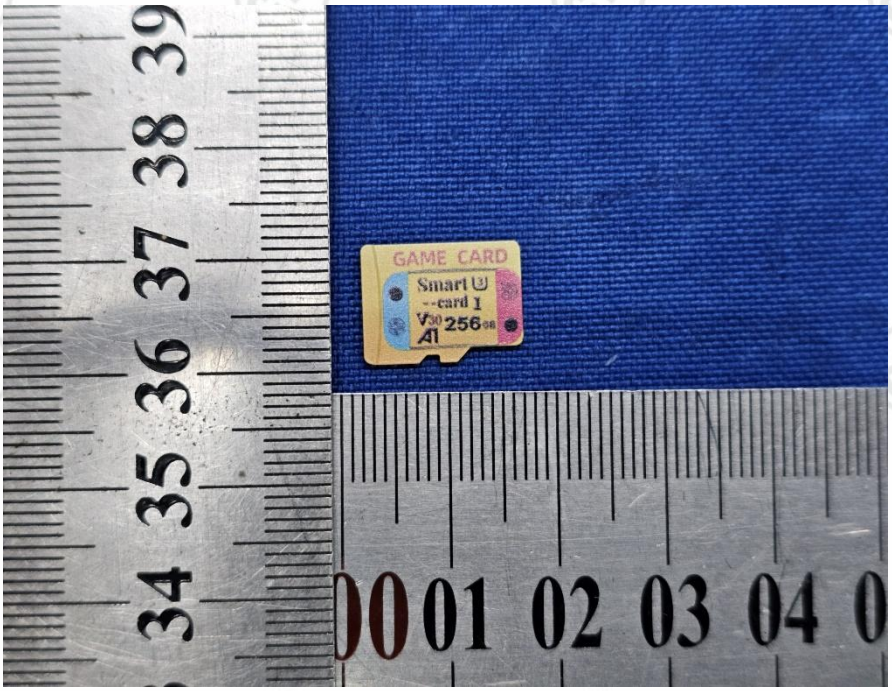


Continuous RF electromagnetic radiated field disturbances Test Setup-1

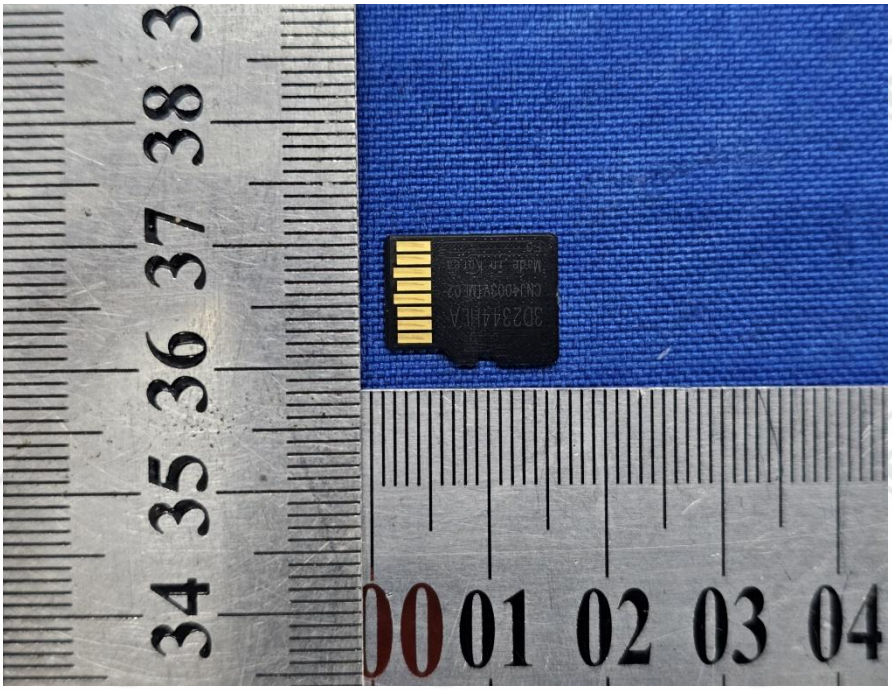
APPENDIX 2 PHOTOGRAPHS OF PRODUCT



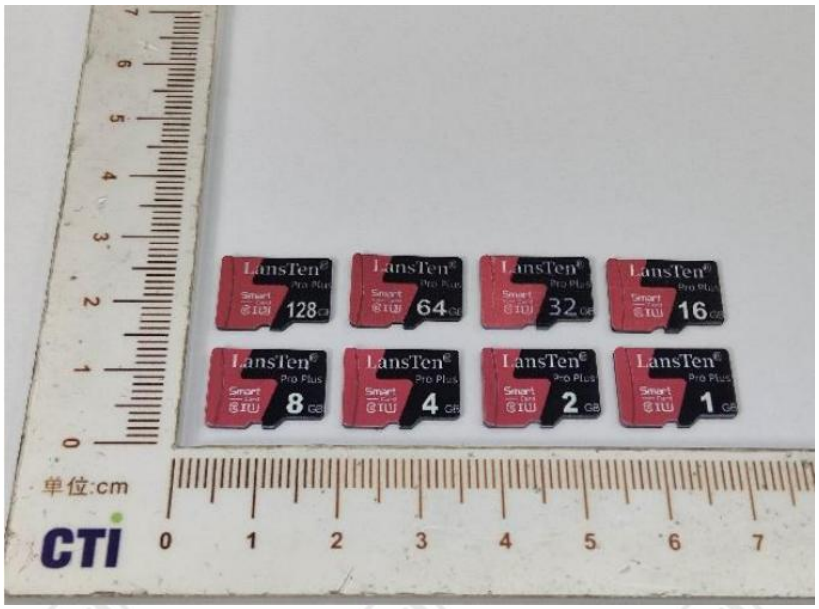
View of Product-01



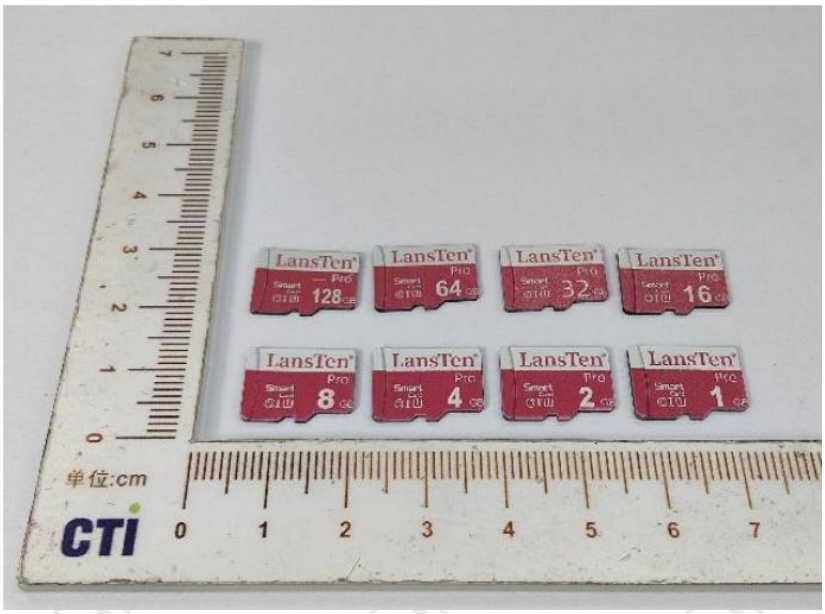
View of Product-02



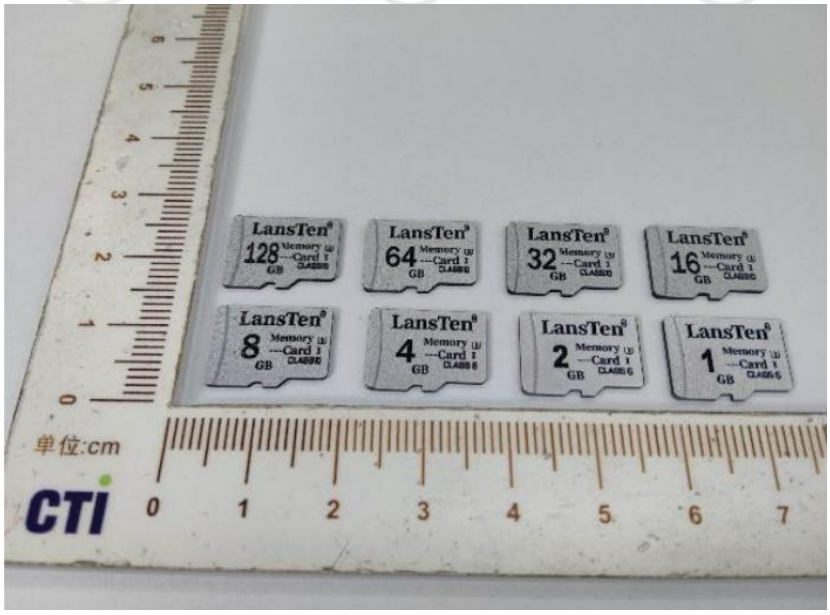
View of Product-03



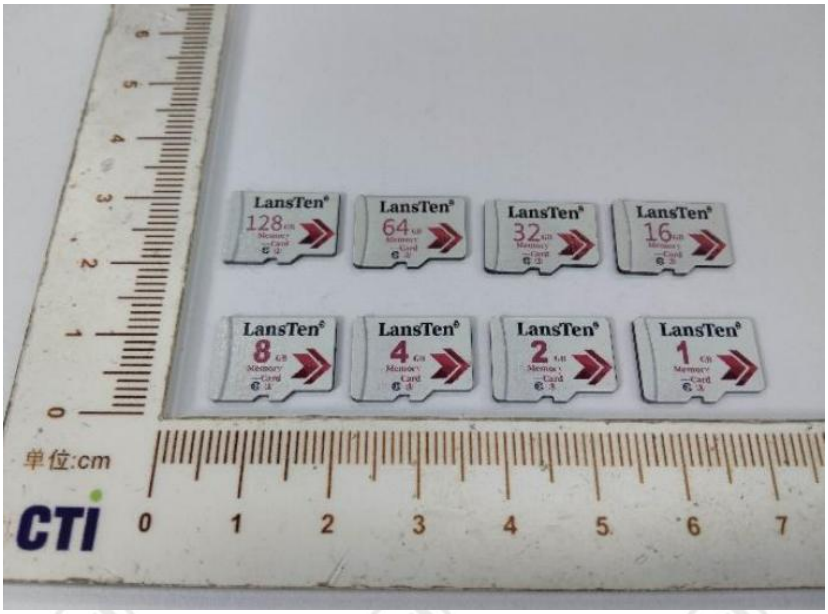
View of Product-04



View of Product-05



View of Product-06



View of Product-07



View of Product-08



View of Product-09

Statement

1. This report is considered invalid without approved signature, special seal and the seal on the perforation;

2. The Company Name shown on Report and Address, the sample(s) and sample information was/were provided by the applicant who should be responsible for the authenticity which CTI hasn't verified;

3. The result(s) shown in this report refer(s) only to the sample(s) tested;

4. Unless otherwise stated,the decision rule for conformity reporting is based on Binary Statement for Simple Acceptance Rule stated in ILAC-G8:09/2019/CNAS-GL015:2022;

5. Without written approval of CTI, this report can't be reproduced except in full;

*** End of Report ***